

SC146

High-reliability discrete products and engineering services since 1977

SILICON BIDIRECTIONAL THYRISTORS

FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Repetitive peak off-stage voltage, gate open			
SC146B		200	
SC146D	V _{DRM}	400	Volts
SC146E	V DRM	500	VOILS
SC146M		600	
SC146N		700	
RMS on-state current (T _c = 80°C)	I _{T(RMS)}	10	Amps
Peak non-repetitive surge current (One Cycle, 60Hz)	I _{TSM}	120	Amps
Circuit fusing considerations	l ² t		A ² s
(t = 8.3ms)		60	AS
Peak gate power (pulse width = 10μ s)	P _{GM}	10	Watts
Average gate power (T _c = 80°C, t = 8.3ms)	P _{G(AV)}	0.5	Watts
Peak gate current (pulse width = 10µs)	I _{GM}	3.5	Amps
Peak gate voltage	V _{GM}	10	Volts
Operating junction temperature range	T,	-40 to +100	°C
Storage temperature range	T _{stg}	-40 to +125	°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal resistance, junction to case	R _{ejc}	1.5	°C/W

ELECTRICAL CHARACTERISTICS (T_c = 25°C and either polarity of MT2 to MT1 voltage unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
Peak off state current					
(V _D = V _{DRM} , gate open)					mA
T _c = 25°C	I _{DRM}	-	-	0.1	IIIA
T _c = 100°C		-	-	0.5	
Peak on-state voltage	V _{TM}				Volts
$(I_{TM} = 14A \text{ peak, pulse width} \le 1 \text{ ms, duty cycle} \le 2\%)$	¥ ™	-	-	1.65	VOILS
Critical rate of rise of off-state voltage	dv/dt				Muc
(V_D = Rated V_{DRM} , gate open, exponential waveform, T_C = 100°C)	uv/ut	-	50	-	V/µs
Critical rate of rise of commutating voltage					
($I_{T(RMS)}$ = Rated $I_{T(RMS)}$, V_D = Rated V_{DRM} , commutating di/dt = 5.4A/ms, gate open, T_C = 80°C)	dv/dt(c)	4	-	-	V/µs
DC gate trigger current (continuous dc)					
(V _D = 12V, trigger mode)					
MT2(+), G(+); MT2(-), G(-); R _L = 100Ω	-		-	50	mA
MT2(+), G(-); $R_L = 50\Omega$	I _{GT}	-	-	50	IIIA
MT2(+), G(+); MT2(-), G(-); R _L = 50 ^Ω , T _C = -40°C		-	-	80	
MT2(+), G(-);R _L = 25Ω, T _C = -40°C		-	-	80	



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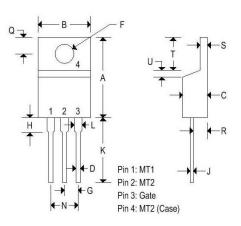
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DC gate trigger voltage (continuous dc)					
(V _D = 12V, trigger mode)					
MT2(+), G(+); MT2(-), G(-); R _L = 100Ω		-	-	2.5	
MT2(+), G(-); $R_L = 50\Omega$	V _{GT}	-	-	2.5	Volts
MT2(+), G(+); MT2(-), G(-); $R_L = 50\Omega$, $T_C = -40^{\circ}C$		-	-	3.5	
MT2(+), G(-); $R_L = 25\Omega$, $T_C = -40^{\circ}C$		-	-	3.5	
(V _D = Rated V _{DRM} , R _L = 1000 Ω , T _C = 100°C) all polarities		0.2	-	-	
Holding current	I _H				mA
(V _D = 24V, I_T = 0.5A, pulse width = 1ms, duty cycle \leq 2%,					
gate trigger source 7V, 20Ω)					
T _c = 25°C		-	-	50	
T _c = -40°C		-	-	100	
Latching current	١				mA
(V _D = 24V)					
Trigger source: 15V, 100 Ω , trigger mode)					
MT2(+), G(+); MT2(-), G(-)		-	-	100	
MT2(+), G(-)		-	-	200	
MT2(+), G(+); MT2(-), G(-), T _c = -40°C		-	-	200	
MT2(+), G(-), T _c = -40°C		-	-	400	

MECHANICAL CHARACTERISTICS

Case	ТО-220АВ
Marking	Alpha-numeric
Pin out	See below



	TO-220AB					
	Inches		Millin	neters		
	Min	Max	Min	Max		
Α	0.575	0.620	14.600	15.750		
В	0.380	0.405	9.650	10.290		
С	0.160	0.190	4.060	4.820		
D	0.025	0.035	0.640	0.890		
F	0.142	0.147	3.610	3.730		
G	0.095	0.105	2.410	2.670		
Н	0.110	0.155	2.790	3.930		
J	0.014	0.022	0.360	0.560		
К	0.500	0.562	12.700	14.270		
L	0.045	0.055	1.140	1.390		
Ν	0.190	0.210	4.830	5.330		
Q	0.100	0.120	2.540	3.040		
R	0.080	0.110	2.040	2.790		
S	0.045	0.055	1.140	1.390		
T	0.235	0.255	5.970	6.480		
U	14	0.050	-	1.270		
٧	0.045		1.140	-		
Ζ	-	0.080		2.030		



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